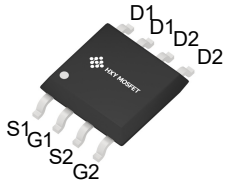
Description

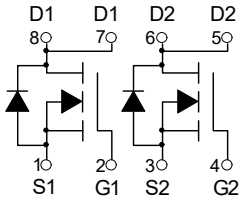
The Si4288DY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8
(SO-8)

General Features

V_{DS} = 40V I_D = 12A
$R_{DS(ON)}$ < 16mΩ @ V_{GS}=10 V
$R_{DS(ON)}$ < 24mΩ @ V_{GS}=4.5V



Dual N-Channel MOSFET

Application

Battery protection
Load switch
Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
Si4288DY	SOP-8(SO-8)	HXY MOSFET	3000

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Drain Current, V_{GS} @ 4.5V[3]	12	A
I_D@T_A=70℃	Drain Current, V_{GS} @ 4.5V[3]	7	A
I_{DM}	Pulsed Drain Current[1]	40	A
P_D@T_A=25℃	Total Power Dissipation	2.9	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	65	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=8A	-	12.0	16	mΩ
		V_{GS}=4.5V, I_D=4A	-	18.9	24	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=8A	33	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=20V,V_{GS}=0V, F=1.0MHz	-	964	-	PF
Output Capacitance	C_{oss}		-	109	-	PF
Reverse Transfer Capacitance	C_{rss}		-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=20V, R_L=2.5Ω V_{GS}=10V,R_{GEN}=3Ω	-	5.5	-	nS
Turn-on Rise Time	t_r		-	14	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	24	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	V_{DS}=20V,I_D=8A, V_{GS}=10V	-	22.9	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	nC
Gate-Drain Charge	Q_{gd}		-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=9A	-	0.8	1.2	V

Typical Electrical and Thermal Characteristics (Curves)

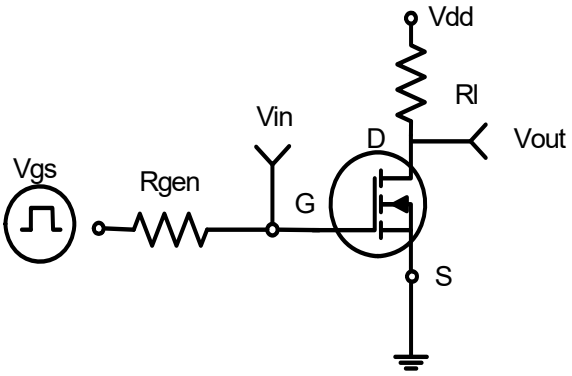


Figure 1:Switching Test Circuit

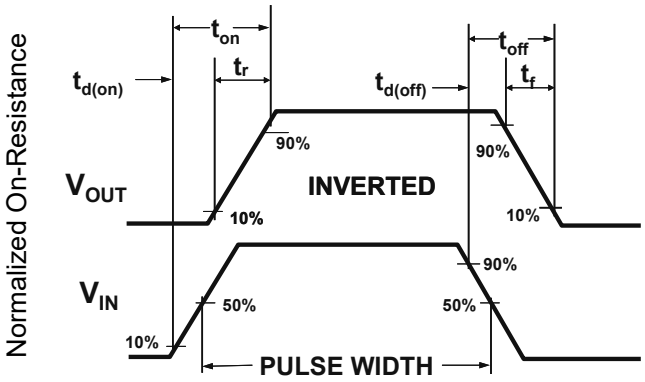


Figure 2:Switching Waveforms

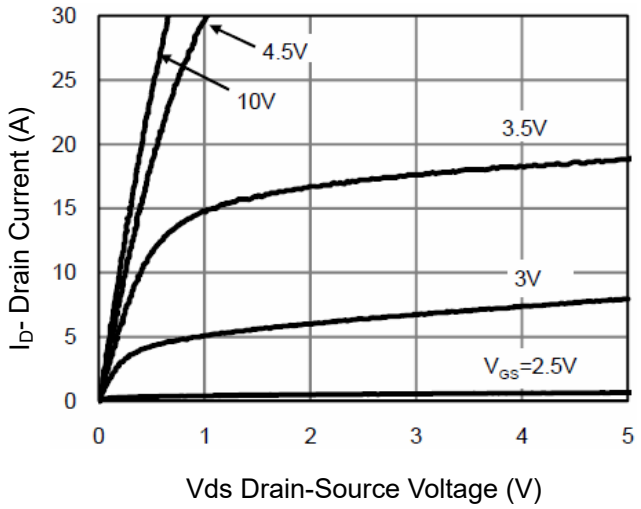


Figure 3 Output Characteristics

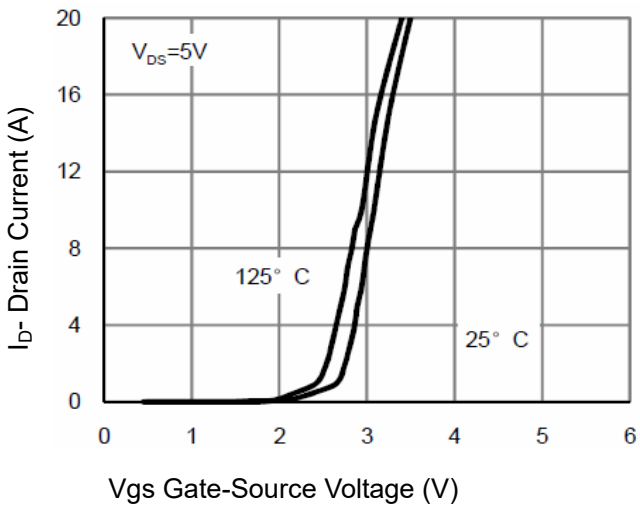


Figure 4 Transfer Characteristics

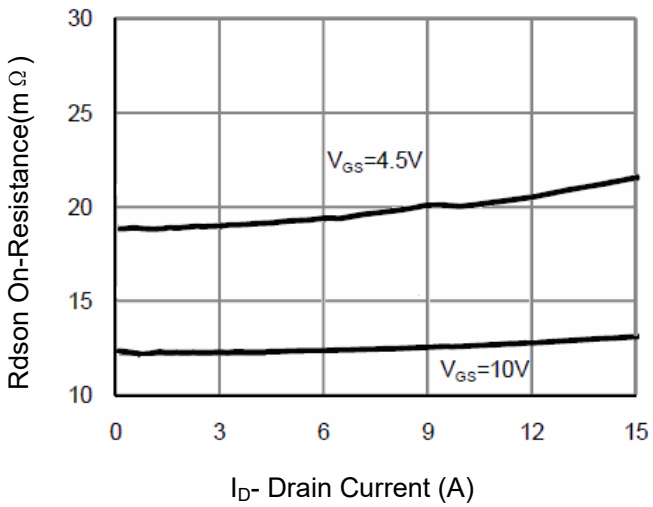


Figure 5 Drain-Source On-Resistance

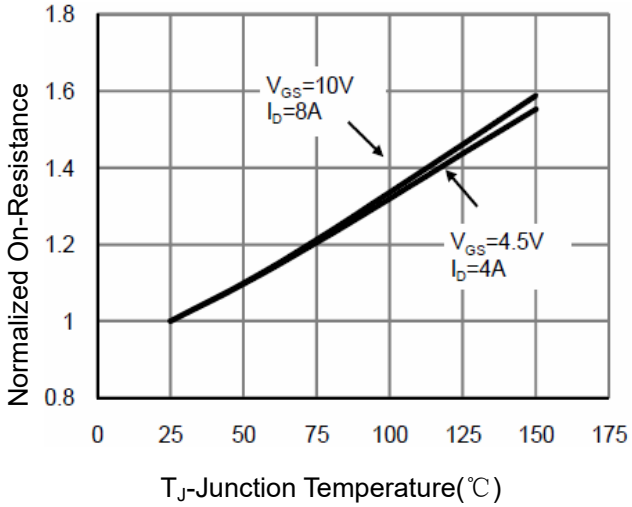
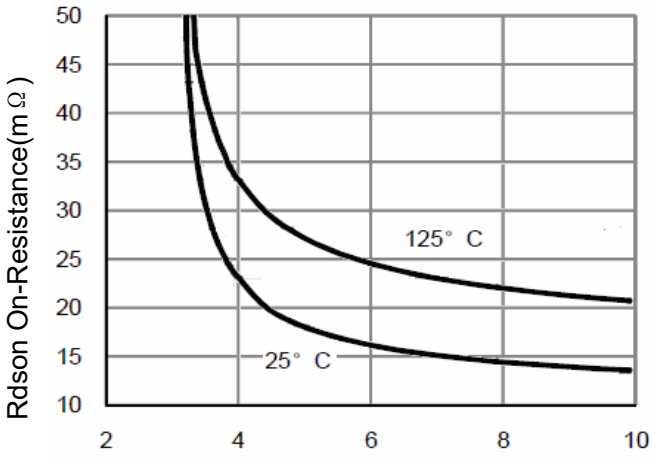
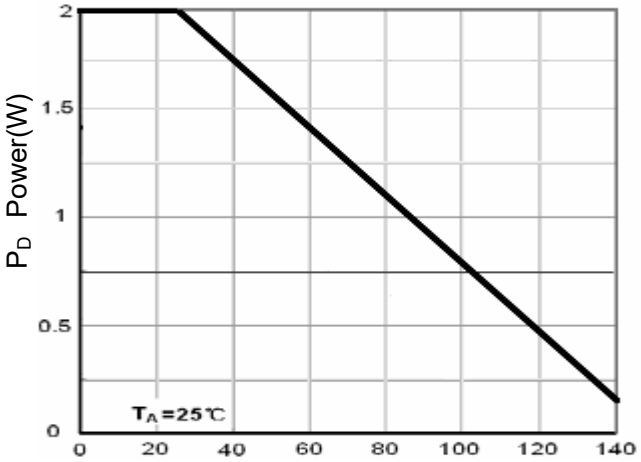


Figure 6 Drain-Source On-Resistance



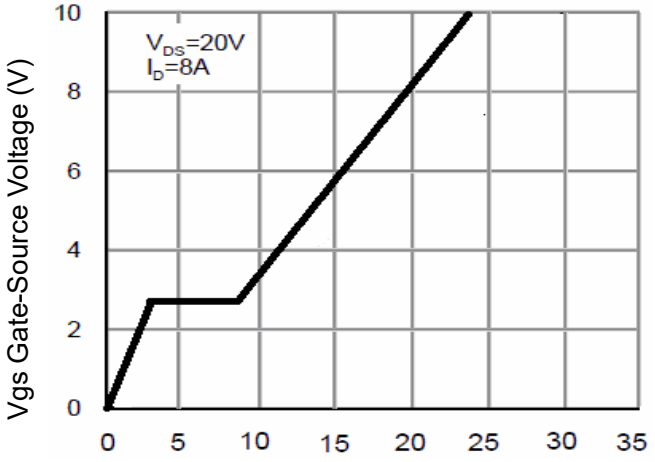
Vgs Gate-Source Voltage (V)

Figure7 Rdson vs Vgs



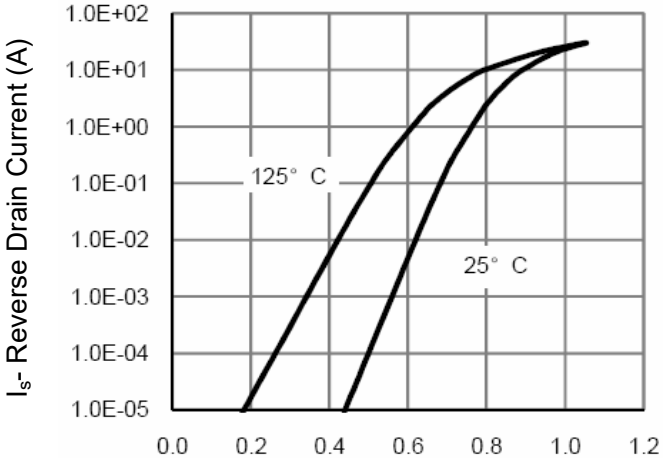
T_J-Junction Temperature(℃)

Figure 8 Power Dissipation



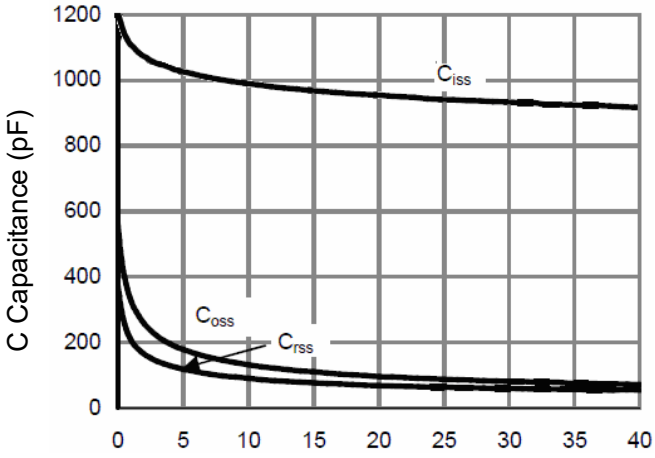
Qg Gate Charge (nC)

Figure 9 Gate Charge



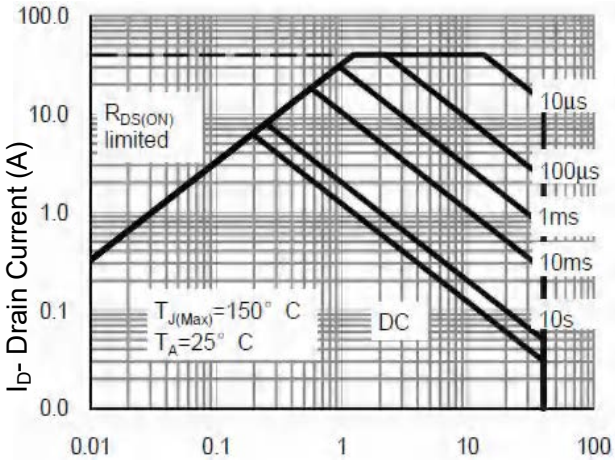
Vds Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

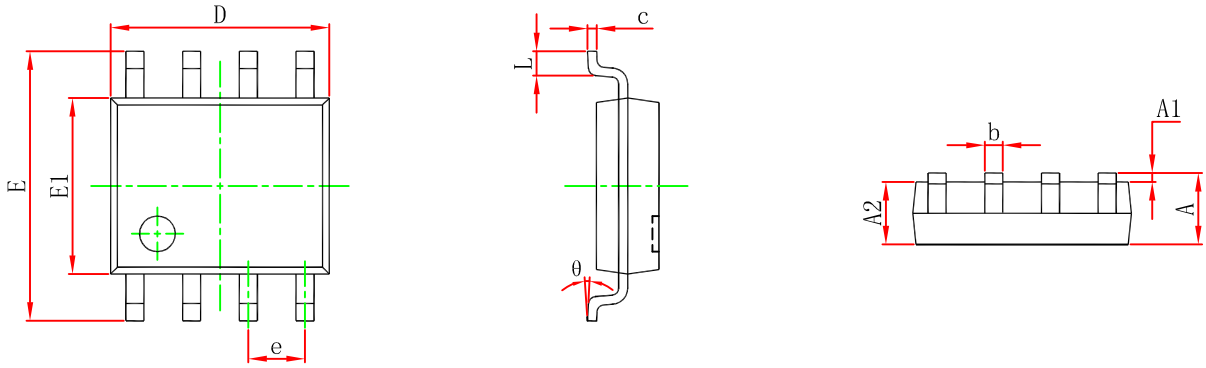
Figure 11 Capacitance vs Vds



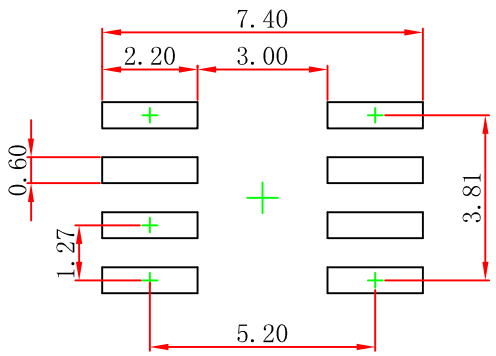
Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area

SOP-8(SO-8) Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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